IN THE CLAIMS

1. (Currently amended) A method of classifying defect chips, said method comprising:

finding defect locations a location of a first defect on a wafer using a semiconductor defect inspection instrument;

analyzing the defect a composition of the first defect using the semiconductor defect inspection instrument; and

marking defect locations the location of the first defect on a wafer map using the different types of marks a first mark to identify of different types of defects a type of the first defect.

- 2. (Currently amended) The method according to claim 1, wherein different types of marks differ according to shape marking the location using a first mark comprises using a first mark with a shape that is dependent upon the type of the first defect.
- 3. (Currently amended) The method according to claim 1, wherein different types of marks are color differ according to color marking the location using a first mark comprises using a first mark with a color that is dependent upon the type of the first defect.
- 4. (Currently amended) The method according to claim 1, further comprising graphing defect characteristics a characteristic of the first defect concurrently with marking defect locations the location on the wafer map.
- 5. (Currently amended) The method according to claim 1, further comprising storing and analyzing defect characteristics a characteristic of the first defect electronically using software.
- 6. (Currently amended) The method according to claim 1, further comprising: using the marks on the wafer map to prepare graphs to assist in statistically analyzing the defects.

finding a location of a second defect on the wafer using the semiconductor defect inspection instrument;

analyzing a composition of the second defect using the semiconductor defect
inspection instrument; and
marking the location of the second defect on the wafer map using a second mark to
identify a type of the second defect; and
using the first and second marks to prepare a graph to assist in statistically analyzing
the first and second defects.

7. (Currently amended) A wafer defect map, comprising:

a schematic representation of a semiconductor wafer, including that includes demarcations corresponding to the location of chip boundaries; and

a plurality of markings, each marking corresponding to a wafer defect on the semiconductor wafer, the marking identifying a type of the defect,

wherein locations a location of the markings marking on the wafer map correspond corresponding to locations a location of the defects defect on the wafer, and wherein each marking is configured to identify a type of defect.

- 8. (Currently amended) The wafer defect map according to claim 7, wherein each the marking is configured to identify a the type of the defect by using a color that is associated with that the type of the defect.
- 9. (Currently amended) The wafer defect map according to claim 7, wherein the markings have different shapes depending on defect type the marking configured to identify the type of the defect by using a shape that is associated with the type of the defect.
- 10. (Currently amended) The wafer defect map according to claim 7, wherein the location of the defect and the type of wafer defects the defect is determined using a semiconductor defect inspection instrument.
- 11. (Currently amended) A method of statistically analyzing defects on a semiconductor wafer to improve yield, said method comprising:

identifying a <u>defect</u> location and <u>a defect</u> type of wafer defects for each of at least two <u>defects on a semiconductor wafer</u>;

determining a chemical composition of the wafer each of the at least two defects;

preparing a wafer defect map to visually represent the defect location and the defect type for each of the at least two wafer defects; and

preparing one or more charts and/or graphs to statistically represent defect characteristics

statistically representing the at least two defects with at least one visual aid.

- 12. (Currently amended) The method according to claim 11, wherein markings are placed further comprising, for each of the at least two defects, placing a marking on the wafer defect map that corresponds to the defect location on the wafer defect map corresponding to defect locations.
- 13. (Currently amended) The method according to claim 12, wherein preparing a wafer defect map to visually represent the location and type of the wafer defects comprises: placing a marking comprises using marks on the wafer defect map a marking that are assigned a color is color-coded based upon the type of the wafer defect type.
- 14. (Currently amended) The method according to claim 11, wherein identifying a the defect location and the defect type of wafer defects comprises using an optical or scanning electron microscope to identify the location and type of wafer defects.
- 15. (Currently amended) The method according to claim 11, wherein determining a chemical composition of the wafer defects comprises performing an AES analysis on each of the at least two defects to determine the compositions thereof.
- 16. (Original) The method according to claim 11, wherein preparing one or more charts and/or graphs statistically representing the at least two defects comprises constructing a table eomprising having columns corresponding to the defect type, defect the chemical composition, a defect cause, and the defect location.
- 17. (Currently amended) The method according to claim 11, wherein preparing one or more charts and/or graphs statistically representing the at least two defects comprises preparing a bar graphs representing the number of graph that represents the at least two defects according to the defect type.

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- 18. (Currently amended) The method according to claim 11, wherein preparing a the wafer defect map to visually represent the location and type of the wafer defects, and preparing one or more charts or graphs to statistically represent defect characteristics are statistically representing the at least two defects is performed electronically.
- 19. (Currently amended) The method according to claim 18, wherein identifying a the defect location and the defect type of wafer defects, and determining a the chemical composition of the wafer each of the at least two defects are is also performed electronically.
- 20. (Currently amended) The method according to claim 11, further comprising analyzing the one or more charts or graphs at least one visual aid to determine appropriate corrective action in a wafer fabrication process.
- 21. (New) A method of statistically analyzing wafer defects on a semiconductor wafer to improve yield, said method comprising:

identifying a location and a type of the wafer defects;

determining a composition of the wafer defects;

preparing a wafer defect map to visually represent the location and the type of the wafer defects; and

preparing a bar graph that represents a number of the wafer defects according to the type of the wafer defects.